

a second region integral with said polishing surface, said second region adapted to frictionally contact said wafer [, said second region adapted to achieve a second process effect such that said wafer polishing machine achieves a customized process effect by selectively moving said wafer frictionally against said first region and said second region.];

a first underlying layer disposed beneath said first region, said first underlying layer adapted to achieve a first polishing effect in said first region;
and

a second underlying layer disposed beneath said second region, said second underlying layer adapted to achieve a second polishing effect in said second region such that said wafer polishing machine achieves a customized process effect by selectively moving said wafer frictionally against said first region and said second region.

Please cancel Claim 2 without prejudice.

3. (Amended) The customized polishing pad of claim [2] 1 wherein said first underlying layer and said second underlying layer have differing amounts of hardness when said wafer is frictionally moved against said polishing pad by said wafer polishing machine.

4. (Amended) The customized polishing pad of claim [2] 1 wherein said first underlying layer and said second underlying layer have differing amounts of thickness when said wafer is frictionally moved against said polishing pad by said wafer polishing machine.

Please cancel claim 5 without prejudice.

6. (Amended) The customized polishing pad of claim [2] 1 further comprising:

an overlying layer included in said polishing pad, said overlying layer forming said polishing surface, said overlying layer coupled to said first underlying layer and said second underlying layer.

8. (Amended) The customized polishing pad of claim [2] 1 wherein said polishing pad is a circular polishing pad and said first region and said second region are concentric within said circular polishing pad.

9. (Amended) The customized polishing pad of claim [2] 1 wherein said polishing pad is a linear polishing pad and said first region and said second region are linearly adjacent within said linear polishing pad.

10. (Amended) A multi-region polishing pad adapted for use in a wafer polishing machine, said multi-region polishing pad comprising:

a polishing pad adapted for use in a wafer polishing machine;
a polishing surface included in said polishing pad, said polishing surface adapted to frictionally contact a wafer in said wafer polishing machine;
a plurality of regions integral with said polishing surface, said plurality of regions each adapted to frictionally contact said wafer, each of said plurality of regions adapted to achieve a specific process effect such that said wafer

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polishing machine achieves a multi-region process effect by selectively moving said wafer frictionally against said plurality of regions[.]; and

a plurality of underlying layers included in said polishing pad, said plurality of underlying layers corresponding to said plurality of regions, each of said plurality of underlying layers adapted to achieve said specific process effect in said plurality of regions.

Please cancel Claim 11 without prejudice.

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12. (Amended) The multi-region polishing pad of claim [11] 10 wherein each of said plurality of underlying layers have differing amounts of hardness when said wafer is frictionally moved against said polishing pad by said wafer polishing machine.

Please cancel Claim 13 without prejudice.

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14. (Amended) The multi-region polishing pad of claim [11] 10 further comprising:

an overlying layer included in said polishing pad, said overlying layer forming said polishing surface, and said overlying layer coupled to each of said plurality of underlying layers.

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16. (Amended) The multi-region polishing pad of claim [11] 10 wherein said polishing pad is a circular polishing pad and said plurality of regions are concentrically adjacent within said circular polishing pad.

17. (Amended) The multi-region polishing pad of claim [11] 10 wherein said polishing pad is a linear polishing pad and said plurality of regions are linearly adjacent within said linear polishing pad.

18. (Amended) In a chemical mechanical polishing (CMP) machine, a method of polishing a wafer, the method comprising the steps of:

a) placing a wafer onto a customized polishing pad on a chemical mechanical polishing machine, said polishing pad having a first region and a second region, said first region having a first underlying layer having a first hardness adapted to achieve a first process effect and said second region having a second underlying layer having a second hardness adapted to achieve a second process effect;

b) polishing said wafer using said first region by frictionally moving said wafer against said first region;

c) polishing said wafer using said second region by frictionally moving said wafer against said second region; and

d) moving said wafer selectively between said first region and said second region such that an optimized polishing effect is achieved by utilizing said first process effect and said second process effect.